Dual N-Channel Trench Power MOSFET

General Description

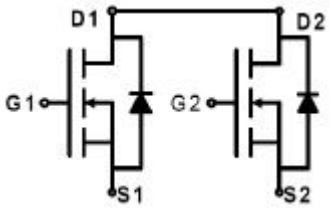
The JTM8810A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching applications.

Features

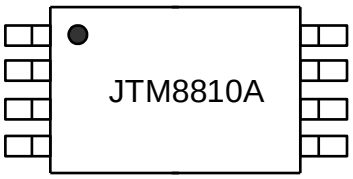
- V_{DS} = 20V,ID =7A
  $R_{DS(ON)}$ < mΩ @ V_{GS} =4.5V
  mΩ @ V_{GS} =2.5V
  -5$R_{DS(ON)}$ <
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery protection
- Load switch
- Power management



Schematic Diagram



Marking and pin Assignment

TSSOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantit
HM	HM	TSSOP8	Ø180mm	8mm	3000 units

Table 1. Absolute Maximum Ratings (T_A=25℃)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V）	20	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±1	V
I_D	Drain Current-Continuous	7	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	25	A
P_D	Maximum Power Dissipation		W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	℃/W

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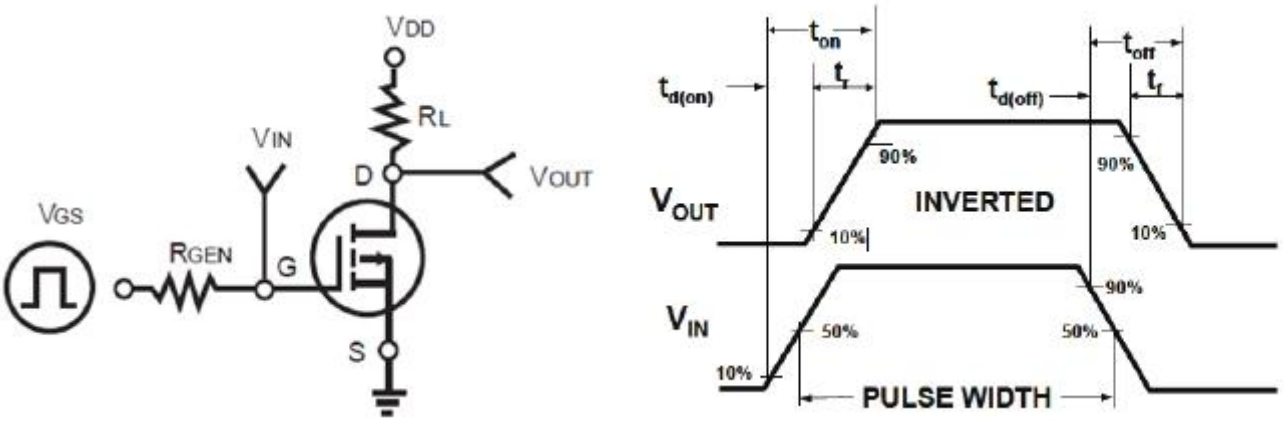
Table 3. Electrical Characteristics (T_A=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	20	21.5		V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=19.5V,V_{GS}=0V			1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±10V,V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	0.5	0.65	1.1	V
g_{FS}	Forward Transconductance	V_{DS}=5V,I_D= A	4	8		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D= A				mΩ
		V_{GS}=2.5V, I_D= A				
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=8V,V_{GS}=0V, f=1.0MHz		605		pF
C_{oss}	Output Capacitance			315		pF
C_{rss}	Reverse Transfer Capacitance			132		pF
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=10V,I_D=1A, V_{GS}=4.5V,R_G=6Ω		11		nS
t_r	Turn-on Rise Time			12		nS
$t_{d(off)}$	Turn-Off Delay Time			36		nS
t_f	Turn-Off Fall Time			32		nS
Q_g	Total Gate Charge	V_{DS}=10V,I_D=4A, V_{GS}=4.5V		10		nC
Q_{gs}	Gate-Source Charge			2.8		nC
Q_{gd}	Gate-Drain Charge			1.8		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)				1.7	A
V_{SD}	Forward on Voltage **(Note 1)**	V_{GS}=0V,I_S=1.7A		0.79	1	V

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Switch Time Test Circuit and Switching Waveforms：



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Power Dissipation

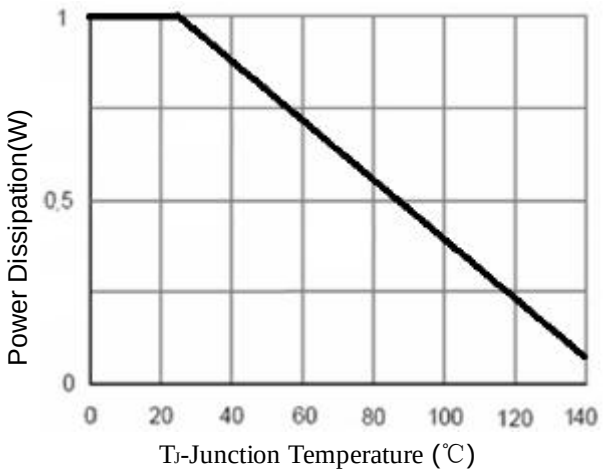


Figure2. Drain Current

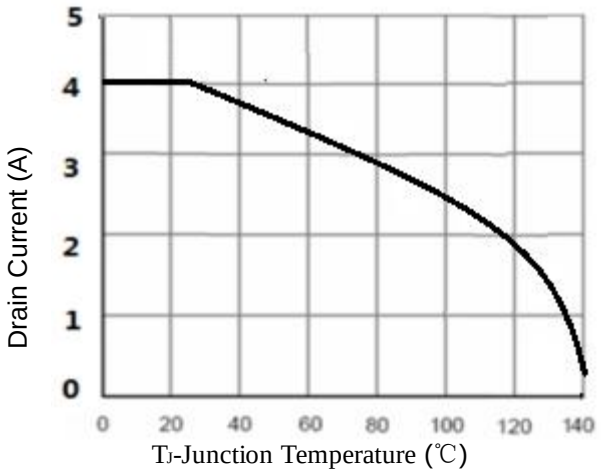


Figure3. Output Characteristics

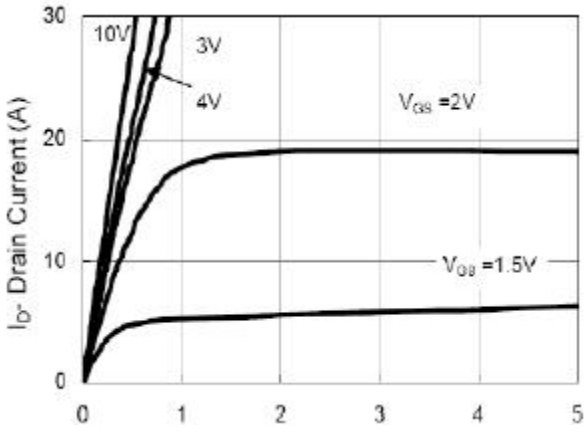


Figure4. Transfer Characteristics

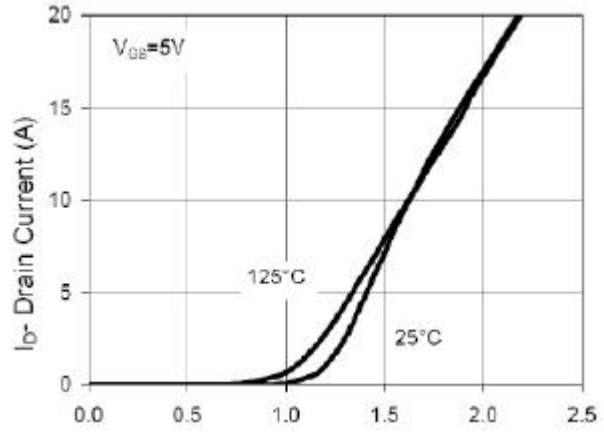


Figure5. Capacitance

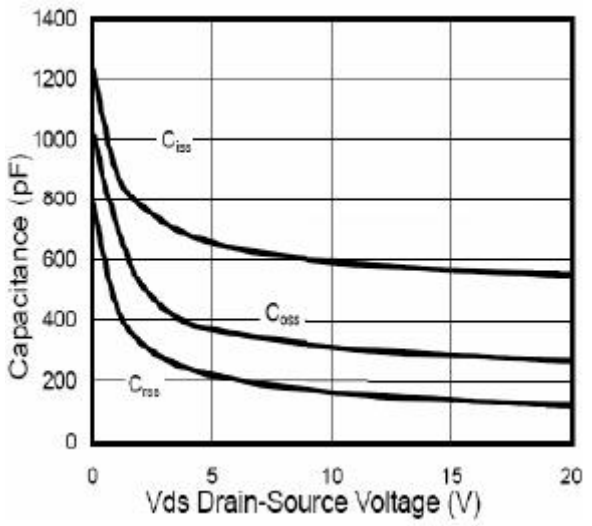


Figure6. $R_{DS(ON)}$ vs Junction Temperature

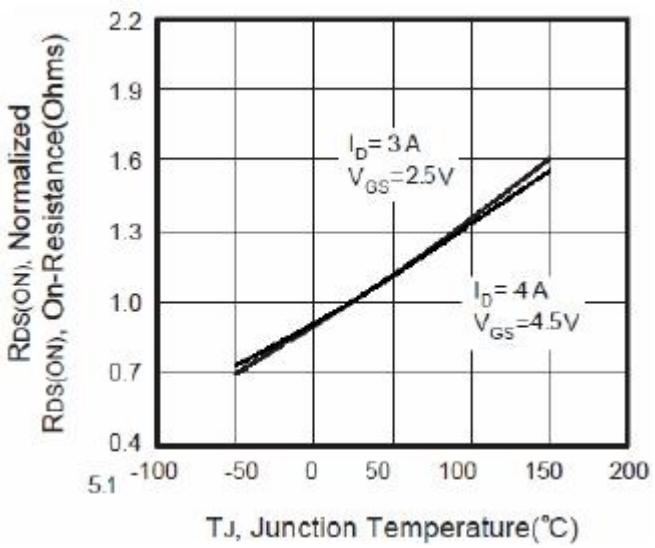


Figure7. Max BV_{DSS} vs Junction Temperature

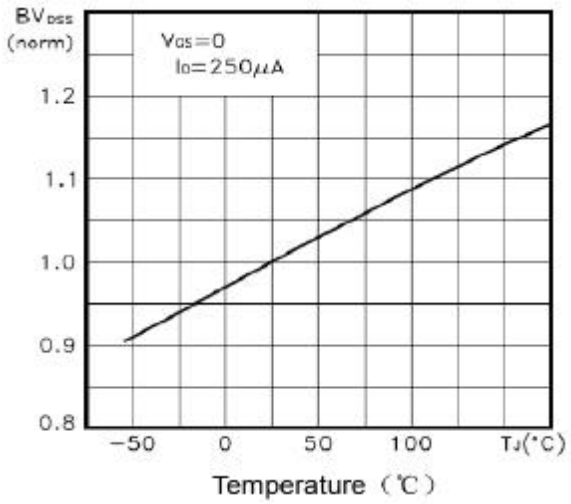


Figure8. $V_{GS(th)}$ vs Junction Temperature

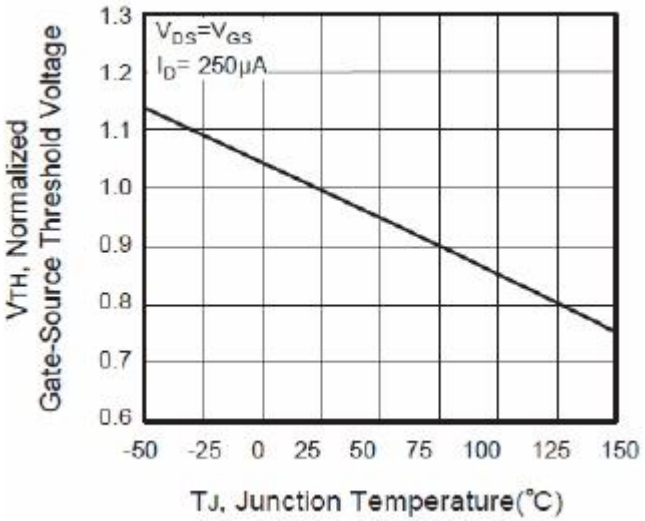


Figure9. Gate Charge Waveforms

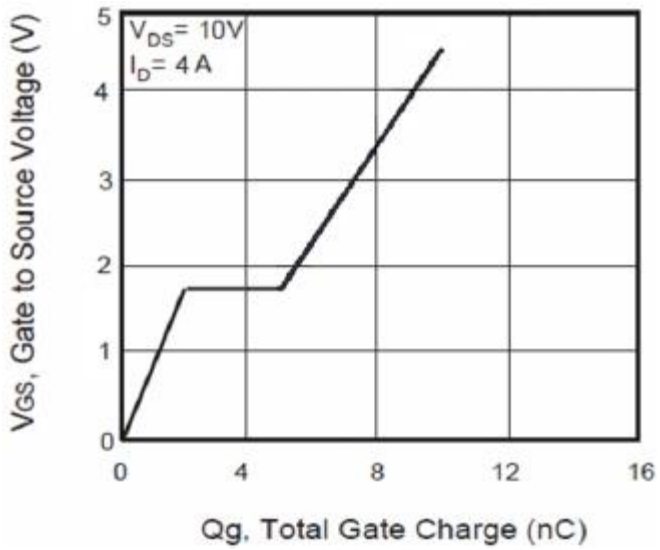
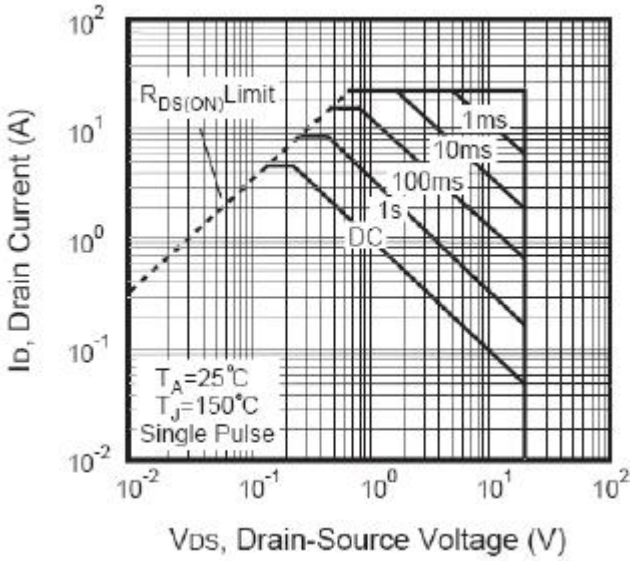
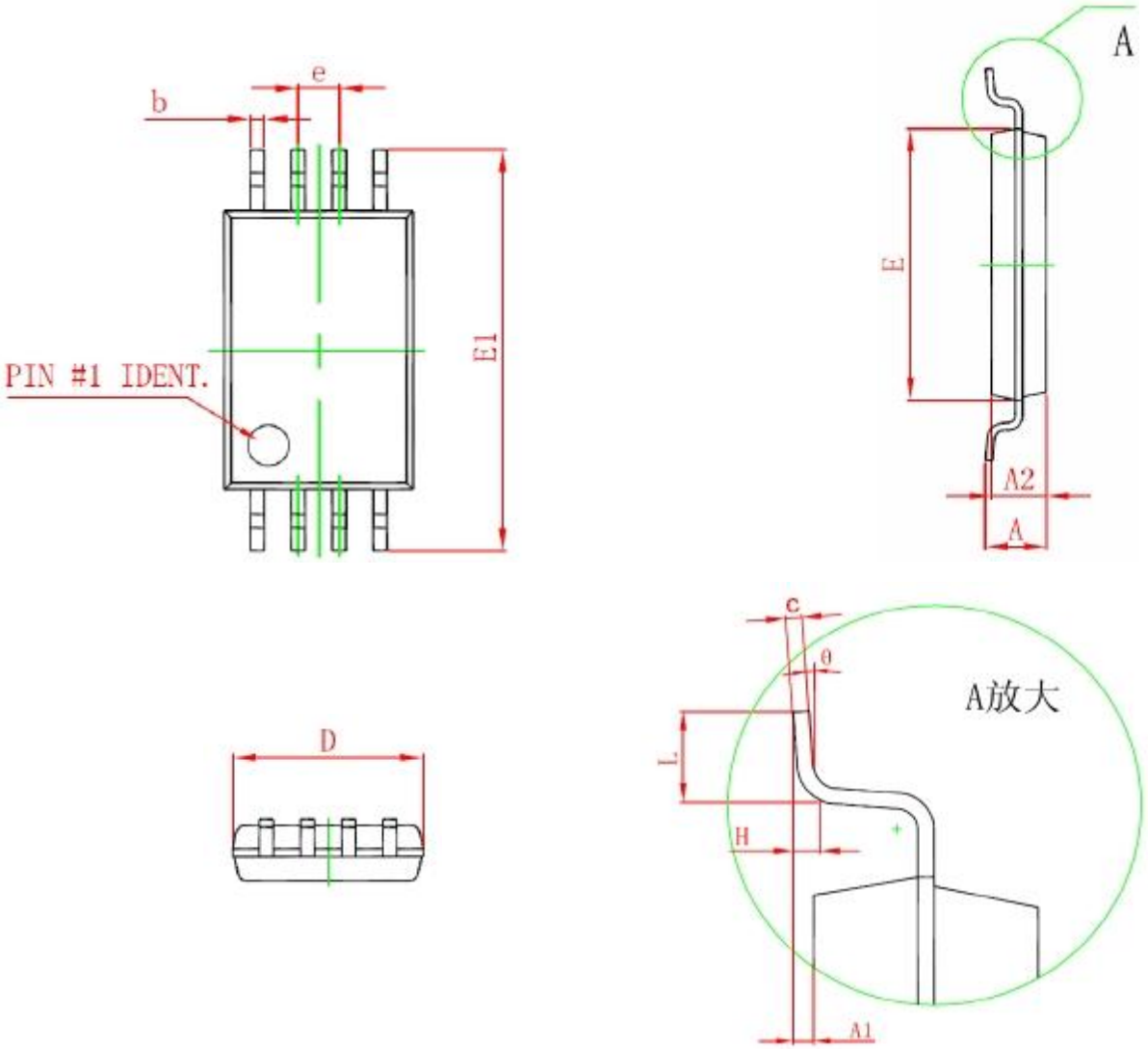


Figure10. Maximum Safe Operating Area



TSSOP-8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
Θ	1°	7°